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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Tomoaki SHINO

SERIAL NUMBER: 10/767,430

GROUP: 2818

FILED: January 30, 2004

EXAMINER: HUYNH, ANDY

FOR: SEMICONDUCTOR DEVICE INCLUDING TRANSISTORS FORMED IN
SEMICONDUCTOR LAYER HAVING SINGLE-CRYSTAL STRUCTURE
ISOLATED FROM SUBSTRATE

REQUEST TO CORRECT TITLE OF INVENTION

MAIL STOP ISSUE FEE
COMMISSIONER FOR PATENTS
P.O. BOX 1450
ALEXANDRIA, VA 22313-1450

SIR:

In the matter of the above-identified application for patent, we hereby request
correction of your records to reflect the correct title of the invention. The title of the
invention should read as follows: **SEMICONDUCTOR DEVICE INCLUDING
TRANSISTORS FORMED IN SEMICONDUCTOR LAYER HAVING SINGLE-
CRYSTAL STRUCTURE ISOLATED FROM SUBSTRATE.**

Respectfully Submitted,

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